

Product Summary

BV_{DSS}	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
60V	2Ω @ $V_{GS} = 5.0\text{V}$	340mA
	2.5Ω @ $V_{GS} = 2.5\text{V}$	300mA

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications:

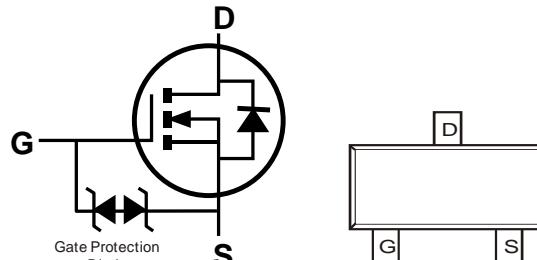
- Motor Control
- Power Management Functions
- Backlighting



SOT323



Top View



Equivalent Circuit

Top View

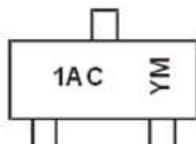
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN61D9UWQ-7	SOT323	3,000/Tape & Reel
DMN61D9UWQ-13	SOT323	10,000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



1AC= Product Type Marking Code

YM = Date Code Marking

Y or YM = Year (ex: E = 2017)

M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025			
Code	E	F	G	H	I	J	K	L	M			
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 7) $V_{GS} = 5.0\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	340 270	mA
	$t < 5\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	400 300	mA
Maximum Continuous Body Diode Forward Current (Note 7)			I_S	0.4	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%) (Note 7)			I_{DM}	1.2	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 6)			P_D	320	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State $t < 5\text{s}$	$R_{\theta JA}$	$R_{\theta JA}$	393	$^\circ\text{C/W}$
				306	
Total Power Dissipation (Note 7)			P_D	440	mW
Thermal Resistance, Junction to Ambient (Note 7)	Steady State $t < 5\text{s}$	$R_{\theta JA}$	$R_{\theta JA}$	289	$^\circ\text{C/W}$
				235	
Operating and Storage Temperature Range			T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	—	1.0	V	$V_{DS} = 10\text{V}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.2	2.0	Ω	$V_{GS} = 5.0\text{V}, I_D = 0.05\text{A}$
			1.6	2.5		$V_{GS} = 2.5\text{V}, I_D = 0.05\text{A}$
			2.5	3.5		$V_{GS} = 1.8\text{V}, I_D = 0.05\text{A}$
Forward Transconductance	$ Y_{fs} $	200	—	—	mS	$V_{DS} = 10\text{V}, I_D = 0.2\text{A}$
Diode Forward Voltage	V_{SD}	—	0.75	1.4	V	$V_{GS} = 0\text{V}, I_S = 115\text{mA}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	28.5	—	pF	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	3.9	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.5	—	pF	
Gate Resistance	R_g	—	65	—	Ω	$f = 1\text{MHz}, V_{GS} = 0\text{V}, V_{DS} = 0\text{V}$
Total Gate Charge	Q_g	—	0.4	—	nC	$V_{GS} = 4.5\text{V}, V_{DS} = 10\text{V},$ $I_D = 250\text{mA}$
Gate-Source Charge	Q_{gs}	—	0.1	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	2.1	—	ns	
Turn-On Rise Time	t_R	—	1.8	—	ns	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V},$ $R_G = 25\Omega, I_D = 200\text{mA}$
Turn-Off Delay Time	$t_{D(OFF)}$	—	14.4	—	ns	
Turn-Off Fall Time	t_F	—	8.4	—	ns	

Notes:

6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
7. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

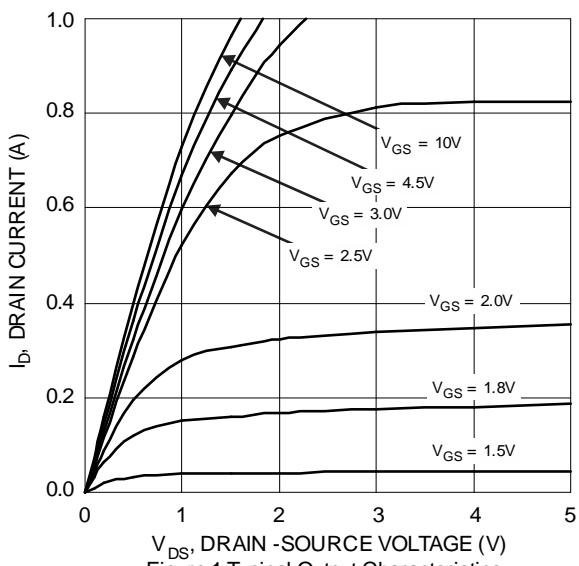


Figure 1 Typical Output Characteristics

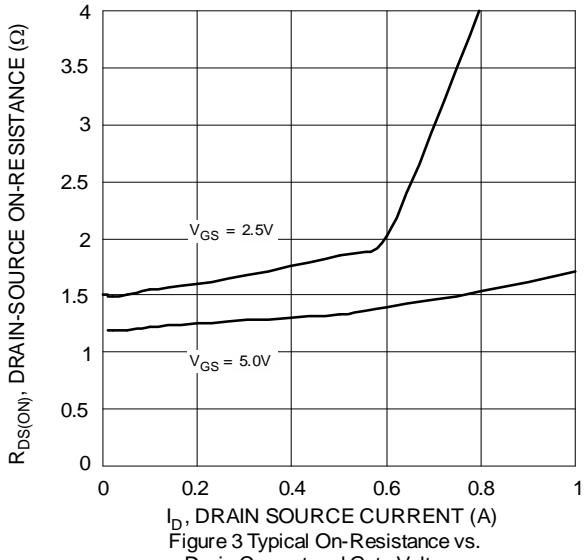


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

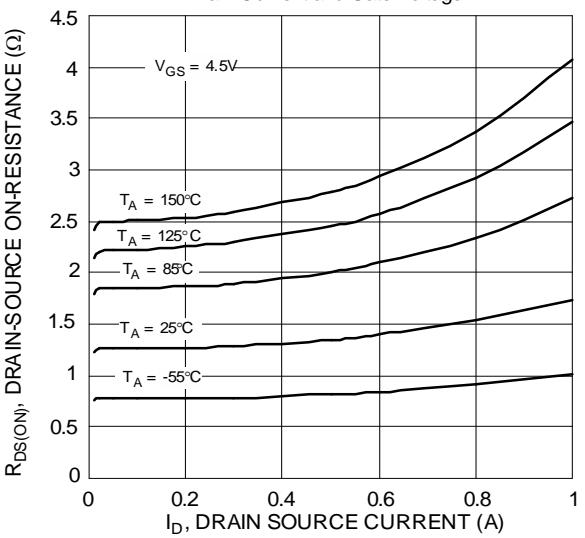


Figure 5 Typical On-Resistance vs.
Drain Current and Temperature

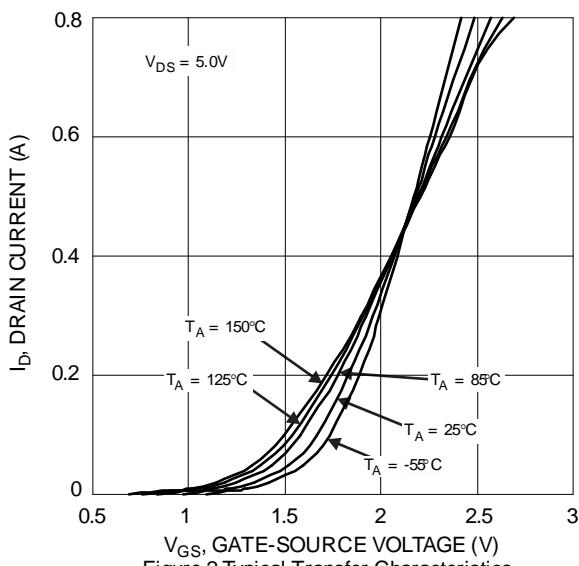


Figure 2 Typical Transfer Characteristics

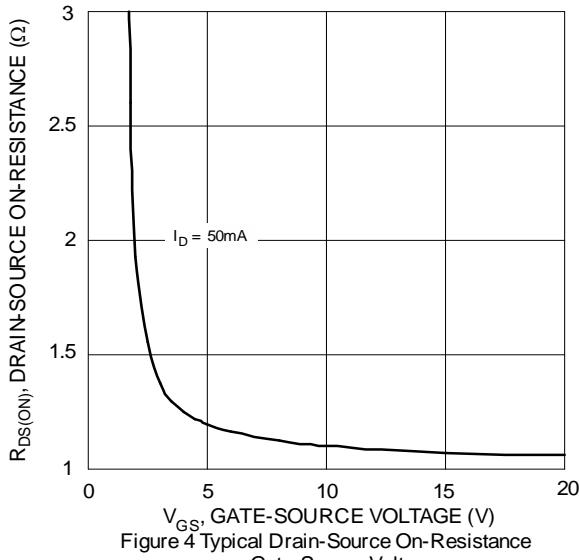


Figure 4 Typical Drain-Source On-Resistance
vs. Gate-Source Voltage

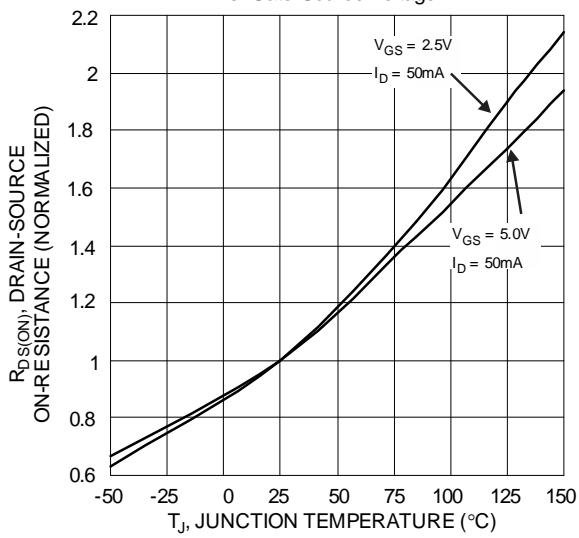


Figure 6 On-Resistance Variation with Junction
Temperature

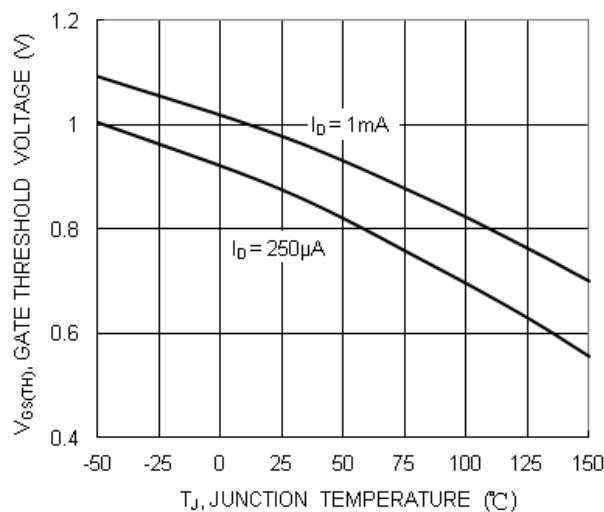


Figure 7. Gate Threshold Variation vs. Junction Temperature

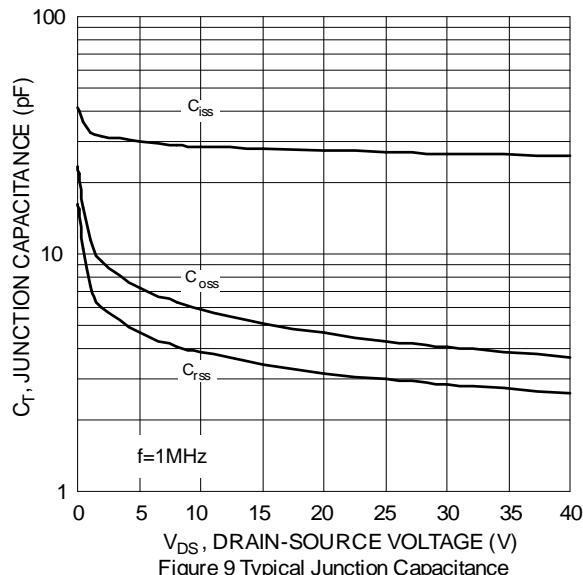


Figure 9 Typical Junction Capacitance

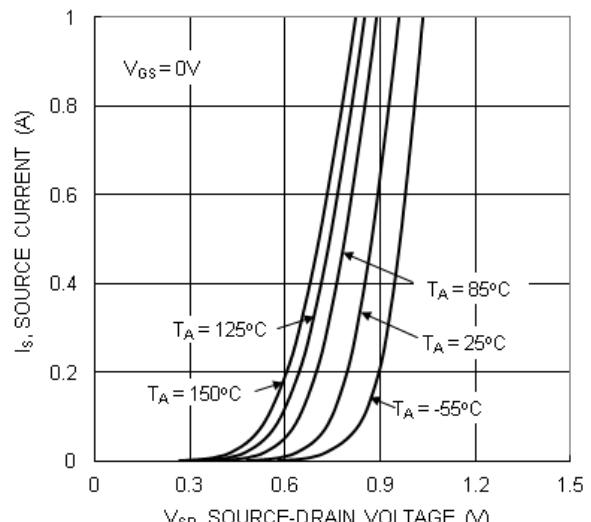


Figure 8. Diode Forward Voltage vs. Current

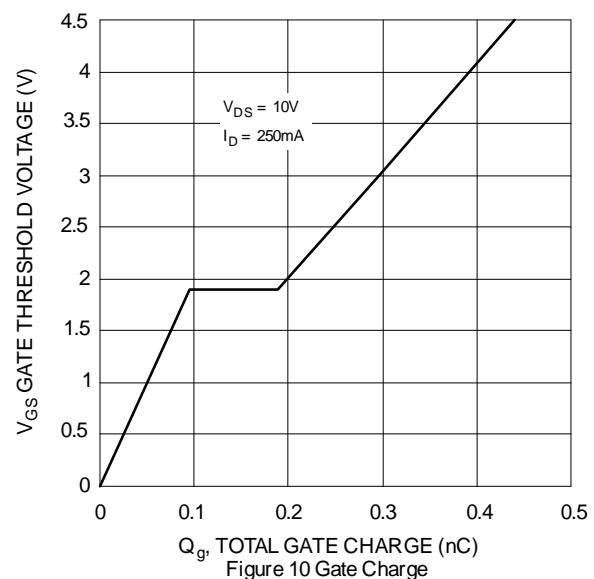


Figure 10 Gate Charge

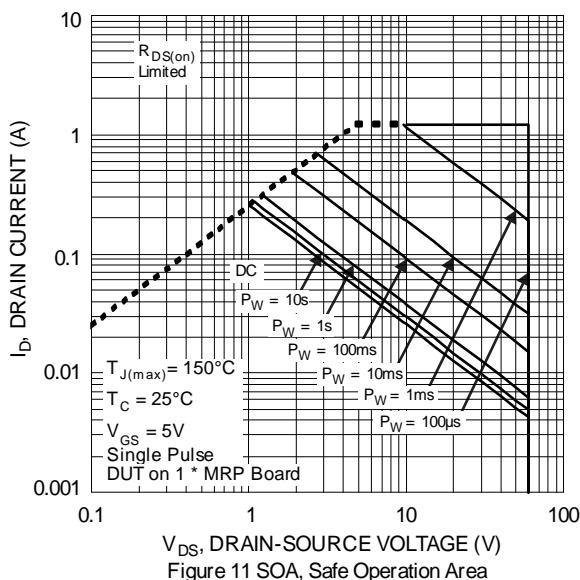
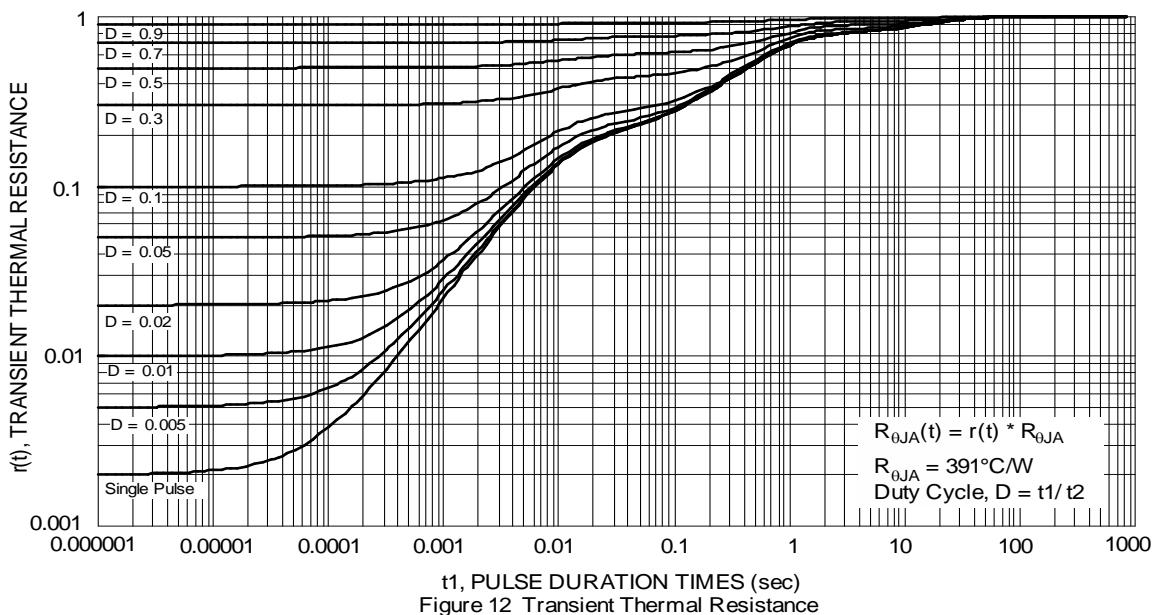
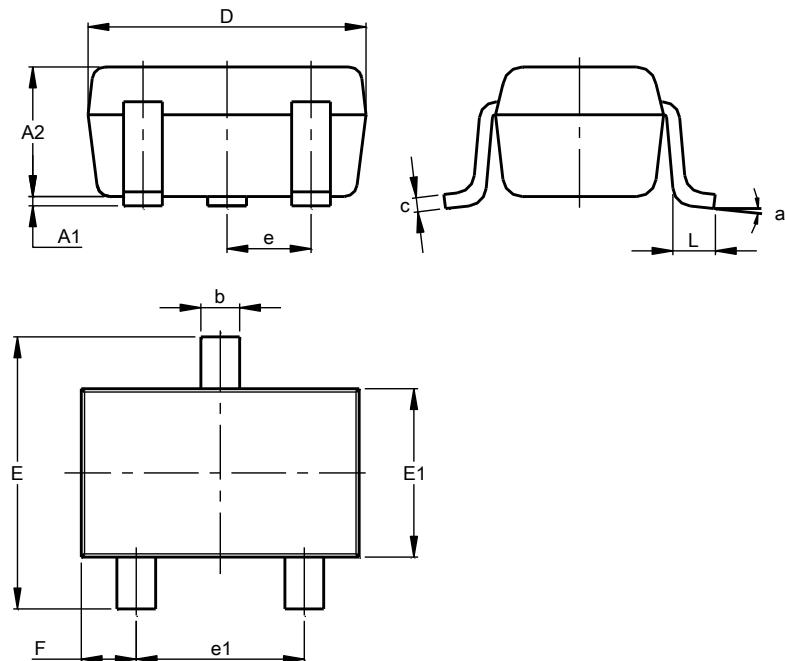


Figure 11 SOA, Safe Operation Area



Package Outline Dimensions

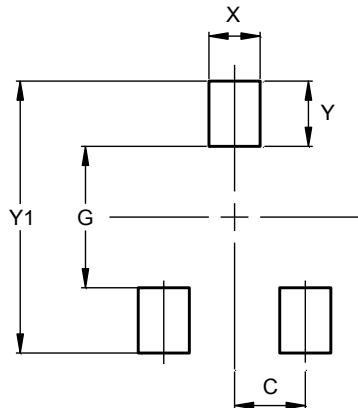
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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